

## CURRENT MODE PWM+PFM CONTROLLER WITH BUILT-IN HIGH VOLTAGE MOSFET

### DESCRIPTION

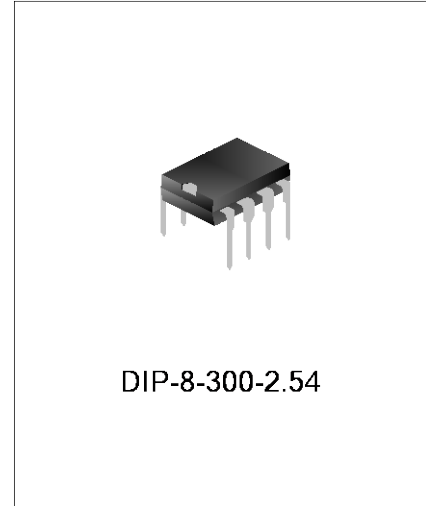
SD6834 is current mode PWM+PFM controller with built-in high-voltage MOSFET used for SMPS.

It features low standby power and low start current. In standby mode, the circuit enters burst mode to reduce the standby power dissipation.

The switch frequency is 25~67KHz decided by the load with jitter frequency for low EMI.

Built-in peak current compensation circuit makes the limit peak current stable even with different input AC voltage. Maximum peak current compensation during power-on reduces pressure on transformer to avoid saturation, the peak current compensation will decrease for balance after power-on. Limit output current can be adjusted through the resistor connected to CS.

It integrates various protections such as undervoltage lockout, overvoltage protection, overload protection, leading edge blanking, primary winding overcurrent protection and thermal shutdown. The circuit will restart until normal if protection occurs.



### APPLICATIONS

- ◆ SMPS

### FEATURES

- ◆ Energy Star 2.0 standard
- ◆ Lower start-up current (3μA)
- ◆ Various switching frequency following load for the high efficiency
- ◆ EMI Frequency jitter for low EMI
- ◆ Overvoltage, primary winding overcurrent, overload and over temperature protections
- ◆ External peak current sense resistor
- ◆ Undervoltage lockout
- ◆ Built-in high voltage MOSFET
- ◆ Auto restart mode
- ◆ Peak current compensation Maximum peak current compensation for initialization to realize the soft start function.
- ◆ Burst mode
- ◆ Cycle by cycle current limit

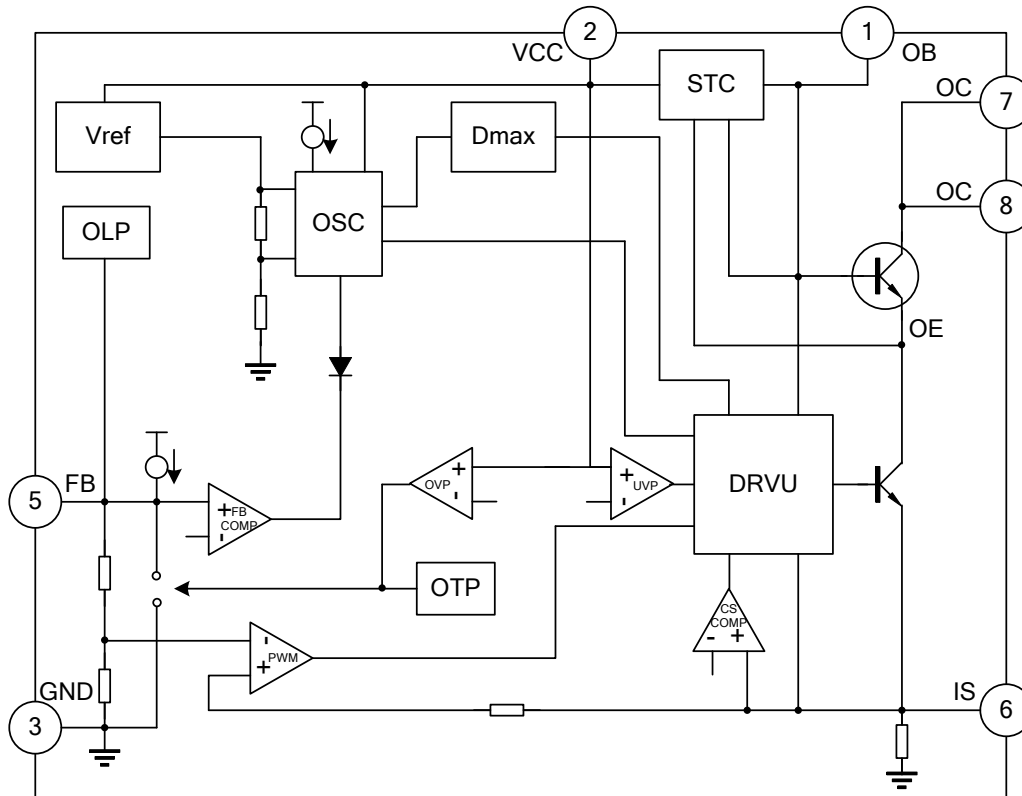
### ORDERING INFORMATION

Part No.	Package	Marking	Hazardous Substance Control	Packaging
SD6834	DIP-8-300-2.54	SD6834	Halogen free	Tube

**TYPICAL OUPUT POWER CAPABILITY**

Part No.	190~265V		85~265V	
	Adapter	Open	Adapter	Open
SD6830	14W	19W	12W	15W

**BLOCK DIAGRAM**



**ABSOLUTE MAXIMUM RATING**

Characteristics	Symbol	Rating	Unit
Drain-Gate Voltage ( $R_{GS}=1M\Omega$ )	$V_{DGR}$	650	V
Gate-Source (GND) Voltage	$V_{GS}$	$\pm 30$	V
Drain Current Pulse <sup>note1</sup>	$I_{DM}$	10	A
Continuous Drain Current ( $T_{amb}=25^{\circ}C$ )	$I_D$	2.5	A
Signal Pulse Avalanche Energy <sup>note2</sup>	$E_{AS}$	140	mJ
Power Supply Voltage	$V_{CC,MAX}$	28	V
Feedback input voltage	$V_{FB}$	-0.3~7	V
Peak current sense voltage	$V_{CS}$	-0.3~2	V
Allowable Power Dissipation	$P_D$	6.3	W
Ambient thermal resistance	$\theta_{ja}$	77	$^{\circ}C/W$
Surface thermal resistance	$\theta_{jc}$	20	$^{\circ}C/W$
Operating Junction Temperature	$T_J$	+150	$^{\circ}C$
Operating Temperature Range	$T_{ORG}$	-25~+85	$^{\circ}C$

Characteristics	Symbol	Rating	Unit
Storage Temperature Range	T <sub>STG</sub>	-55~+150	°C

**Note:** 1. Pulse width is limited by maximum junction temperature;  
2. L=51mH, T<sub>J</sub>=25°C(start).

## ELECTRICAL CHARACTERISTICS (for MOSFET, unless otherwise specified, T<sub>amb</sub>=25°C)

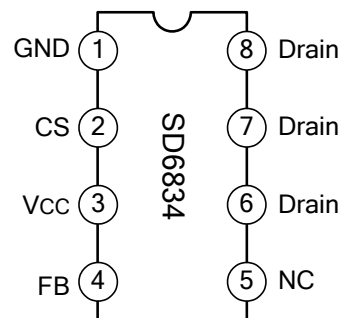
Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =50μA	650	--	--	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =650V, V <sub>GS</sub> =0V	--	--	50	μA
		V <sub>DS</sub> =480V, V <sub>GS</sub> =0V T <sub>amb</sub> =125°C	--	--	200	μA
Static Drain-Source On Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =0.5A	2.3	3.4	4.5	Ω
		V <sub>GS</sub> =10V, I <sub>D</sub> =1.25A	2.5	3.6	4.7	Ω
Input Capacitance	C <sub>ISS</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz	224	320	416	pF
Output Capacitance	C <sub>OSS</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz	28	41	54	pF
Reverse Transfer Capacitance	C <sub>RSS</sub>	V <sub>GS</sub> =0V, V <sub>DS</sub> =25V, f=1MHz	0.9	1.3	1.7	pF
Turn On Delay Time	T <sub>D(ON)</sub>	V <sub>DD</sub> =0.5BV <sub>DSS</sub> , I <sub>D</sub> =25mA	9.1	13	16.9	ns
Rise Time	T <sub>R</sub>	V <sub>DD</sub> =0.5BV <sub>DSS</sub> , I <sub>D</sub> =25mA	21.7	31	40.3	ns
Turn Off Delay Time	T <sub>D(OFF)</sub>	V <sub>DD</sub> =0.5BV <sub>DSS</sub> , I <sub>D</sub> =25mA	12.6	18	23.4	ns
Fall Time	T <sub>F</sub>	V <sub>DD</sub> =0.5BV <sub>DSS</sub> , I <sub>D</sub> =25mA	14	20	26	ns

## ELECTRICAL CHARACTERISTICS (unless otherwise specified, V<sub>CC</sub>=12V, T<sub>amb</sub>=25°C)

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
<b>Undervoltage Section</b>						
Start Threshold Voltage	V <sub>START</sub>		14.5	15.5	17.0	V
Stop Threshold Voltage	V <sub>STOP</sub>		7.5	8.3	9.5	V
<b>Oscillator Section</b>						
Max. Oscillate Frequency	f <sub>OSCMAX</sub>	V <sub>FB</sub> =3V	61	67	73	KHz
Min. Oscillate Frequency	f <sub>OSCMIN</sub>	V <sub>BURL</sub> <V <sub>FB</sub> <V <sub>BURHS</sub>	20	25	30	KHz
Frequency jitter	f <sub>MOD</sub>	Oscillate frequency is the maximum	±1.5	±2.5	±3.5	KHz
Frequency Change With Temperature	--	25°C≤T <sub>amb</sub> ≤+85°C	--	±5	±10	%
Maximum Duty cycle	D <sub>MAX</sub>		72	77	82	%
<b>Feedback Section</b>						
MAX. Feedback Source Current	I <sub>FBMAX</sub>	V <sub>FB</sub> =0V	0.7	0.9	1.1	mA
Shutdown Feedback Voltage (over load protection)	V <sub>SD</sub>		3.8	4.3	4.8	V
Shutdown Feedback Delay Time	T <sub>SD</sub>	FB is increased to 5V from 0V instantly	15	27	40	ms
Shutdown Delay Current	I <sub>DELAY</sub>	V <sub>FB</sub> =5V	3	5.5	8	μA

Characteristics	Symbol	Test conditions	Min.	Typ.	Max.	Unit
<b>CS section</b>						
Max. value of CS	$V_{CSMAX}$		0.7	0.9	1.1	V
<b>Burst mode</b>						
Burst Mode High Voltage	$V_{BURH}$	FB voltage	0.40	0.50	0.60	V
Burst Mode Low Voltage	$V_{BURL}$	FB voltage	0.25	0.35	0.45	V
<b>Protection Section</b>						
Oversvoltage Protection	$V_{OVP}$	$V_{CC}$ voltage	23	24.5	26	V
Over temperature protection	$T_{OTP}$		125	150	--	°C
Leading-edge Blanking Time	$T_{LEB}$		200	325	450	ns
<b>Total Standby Current</b>						
Start Current	$I_{START}$	$V_{CC}$ increases from 0V to 12V	1	3	10	μA
Quiescent Current	$I_{STATIC}$	$V_{FB}=0V$	1.0	1.9	3.0	mA
Operating Current	$I_{OP}$	$V_{FB}=3V$	1.2	2.2	3.2	mA

## PIN CONFIGURATION



**Note:** it is recommended to connect pin 5 to pin Drain for better heat dissipation.

## PIN DESCRIPTION

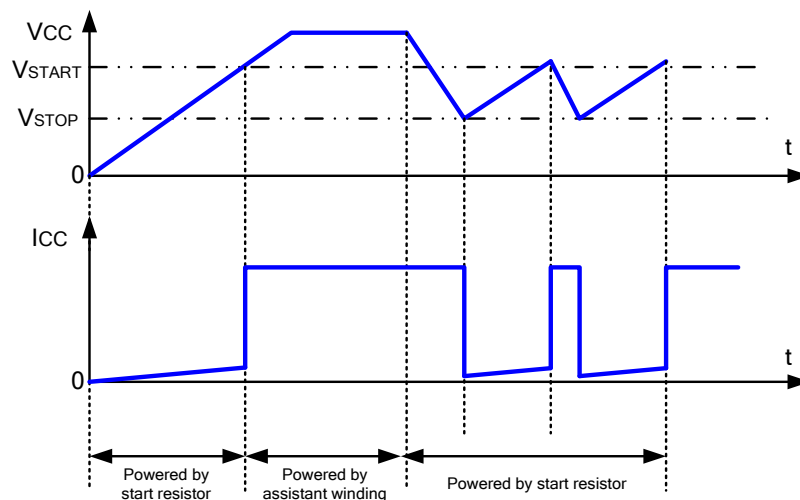
Pin No.	Pin Name	I/O	Function description
1	GND	I	Ground
2	CS	I	Peak current sense pin
3	VCC	I	Power supply pin
4	FB	I/O	Feedback input pin
5	NC	--	NC
6, 7, 8	Drain	O	Drain pins

## FUNCTION DESCRIPTION

SD6834 is designed for off-line SMPS, consisting of high voltage MOSFET, optimized gate driver and current mode PWM+PFM controller which includes frequency oscillator and various protections such as undervoltage lockout, overvoltage protection, overload protection, primary winding overcurrent protection and over temperature protection. Frequency jitter generated from oscillator is used to lower EMI. Burst mode is adopted during light load to lower standby power dissipation, and function of lead edge blanking eliminates the MOSFET error shutdown caused by interference through minimizing MOSFET turning on time. Peak current compensation reduces the pressure on transformer during circuit starts and output power limit can be adjusted by resistor through CS pin. Few peripheral components are needed for higher efficiency and higher reliability and it is suitable for flyback converter and forward converter.

### 1. Under Voltage Lockout and Self-Start

At the beginning, the capacitor connected to pin  $V_{CC}$  is charged via start resistor by high voltage AC and the circuit starts to work if voltage at  $V_{CC}$  is 15.5V. The output and FB source current are shutdown if there is any protection during normal operation and  $V_{CC}$  is decreased because of powering of auxiliary winding. The whole control circuit is shutdown if voltage at  $V_{CC}$  is 8.3V below to lower current dissipation and the capacitor is recharged for restarting.

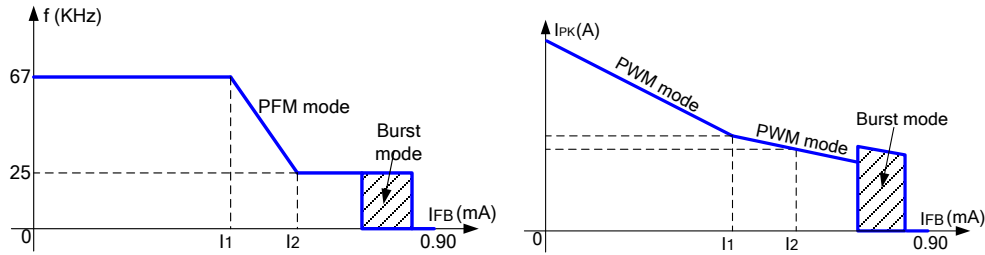


### 2. Frequency Jitter and reduced frequency mode

The oscillation frequency is kept changed for low EMI and decreasing radiation on one frequency. The oscillation frequency changes within a very small range to simplify EMI design. The rule of frequency changing (frequency center is 67KHz):  $\pm 2.5\text{KHz}$  change in 4ms, 63 frequency points in all.

For high efficiency, reduced frequency mode is adopted with two methods:

1. Frequency is reduced according to current output from FB pin. If  $I_{FB}$  is higher than  $I_1$ , the frequency  $f$  decreases from 67KHz and  $f$  is 25KHz when the  $I_{FB}$  increases to  $I_2$  or higher. This is shown in left diagram below.
2.  $I_{PK}$  is changed according to  $I_{FB}$ , shown in right diagram below.



### 3. Peak current sense resistor

The external resistor ( $R_{CS}$ ) connected to pin CS is used for peak current limit, the peak current is given by:

$$I_{PKMAX} = 0.9 / R_{CS}$$

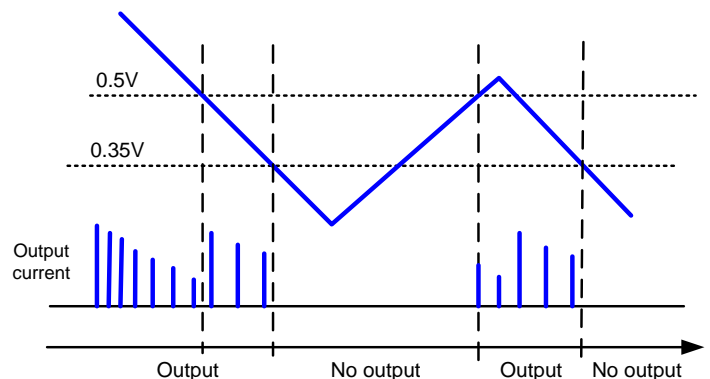
### 4. Peak current compensation and initialization

Generally, limit peak current changes with different inputs. Limit peak current is hold in this circuit because of peak current compensation. Larger peak current compensation for higher input AC voltage, it decreases to zero with light load and no peak current compensation in burse mode.

Maximum peak current compensation during power-on reduces pressure on transformer to avoid saturation, the peak current compensation will decrease for balance after power-on. The duration is decided by the load.

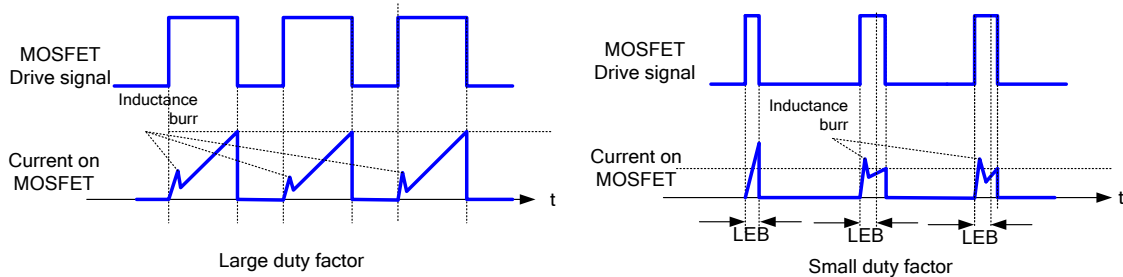
### 5. Burst mode

Working in this mode is to reduce power dissipation. It works normally when FB is 0.5V above, and during  $0.35V < FB < 0.5V$ , there are two different conditions: when FB changes from low to high, there is no action for switch and it is the same with condition of FB lower than 0.35V; the other is that FB changes form high to low, comparison value is increased for increasing turning on time to decrease switch loss. In this mode, switching frequency is down to 25KHz. For this mode, during FB changes form high to low, the output voltage increases (increasing speed is decided by load) because of the high comparison value to decrease FB until it is 0.35V below; when  $FB < 0.35V$ , there is no action for switch and output voltage decreases (decreasing speed is also decided by load) to increase FB voltage. FB voltage is 0.5V below with light load. This is repeated to decrease action of switch for lower power dissipation.



## 6. Leading Edge Blanking

For this current-controlled circuit, there is pulse peak current during the transient of switch turning on and there is an error operation if the current is sampled during this time. And leading edge blanking is adopted to eliminate this error operation. The output of PWM comparator is used for controlling shutdown after the leading edge blanking if there is any output drive.



## 7. Over Voltage Protection

The output is shutdown if voltage at  $V_{CC}$  exceeds the threshold value and this state is kept until the circuit is powered on reset.

## 8. Overload Protection

FB voltage increases if there is overload and the output is shutdown when FB voltage is up to the feedback shutdown voltage. This state is kept until the circuit is powered on reset.

## 9. Cycle By Cycle Peak Current Limit

During each cycle, the peak current value is decided by the comparison value of the comparator, which will not exceed the peak current limited value to guarantee the current on MOSFET will not be larger than the rating current. The output power will not increase if the current reaches the peak value to limit the max. output power.

The output voltage decreases and FB voltage increases if there is overload and corresponding protection occurs.

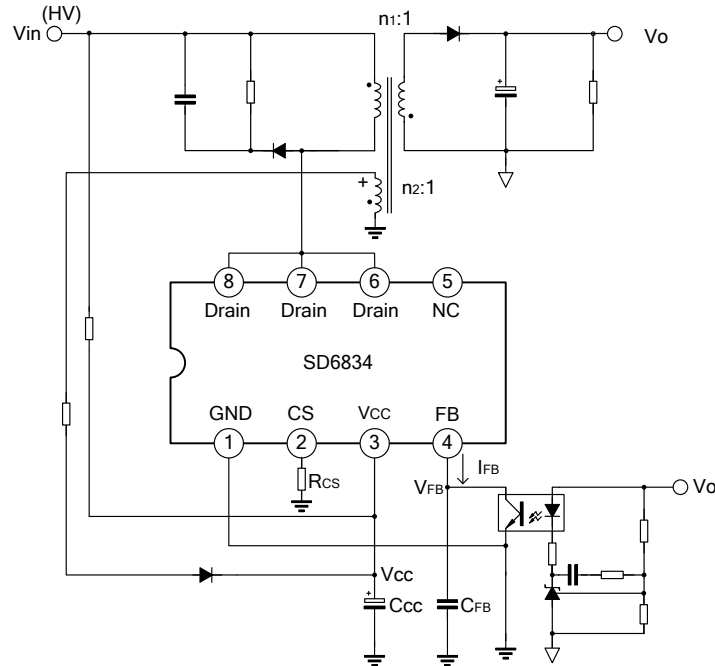
## 10. Primary winding over current protection

If secondary diode is short, or the transformer is short, this protection will occur. At this time, once it is over current in spite of the leading edge blanking (L.E.B) time, protection will begin after 200ns, and is active for every cycle. When the voltage on the pin CS is 1.7V, this protection will occur and the output is shut down. This state is kept until the under voltage occurs, and the circuit will start.

## 11. Thermal Shutdown

If the circuit is over temperature, the over temperature protection will shut down the output to prevent the circuit from damage. This state keeps until the circuit restarts after cooling down.

**TYPICAL APPLICATION CIRCUIT**

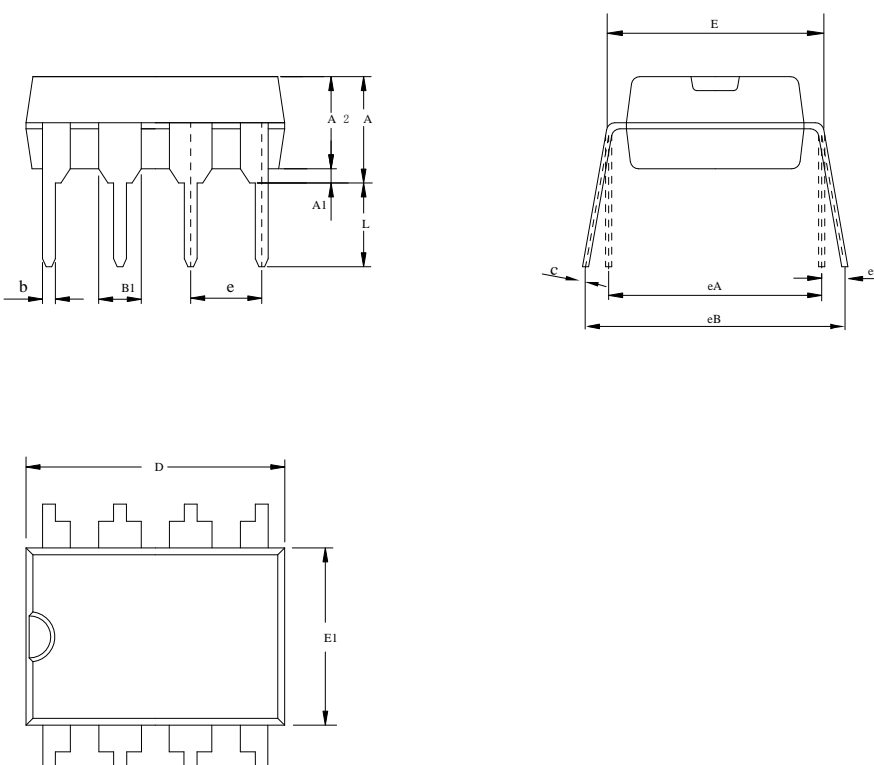


**Note:**

The circuit and parameters are for reference only, please set the parameters of the real application circuit based on the real test.

**PACKAGE OUTLINE**

**DIP-8-300-2.54** **UNIT: mm**



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	—	—	4.10
A1	0.50	—	—
A2	2.90	3.30	3.40
b	0.38	0.46	0.55
B1	1.22	1.52	1.82
c	0.20	0.25	0.32
D	9.00	9.40	9.80
E	7.62	7.87	8.26
E1	6.10	6.35	6.60
e	2.54BSC		
eA	7.62BSC		
eB	7.62	—	9.30
eC	0	—	1.52
L	3.00	—	—





**MOS DEVICES OPERATE NOTES:**

Electrostatic charges may exist in many things. Please take following preventive measures to prevent effectively the MOS electric circuit as a result of the damage which is caused by discharge:

- The operator must put on wrist strap which should be earthed to against electrostatic.
- Equipment cases should be earthed.
- All tools used during assembly, including soldering tools and solder baths, must be earthed.
- MOS devices should be packed in antistatic/conductive containers for transportation.

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Revision History:			
1. Modify the electrical characteristics			

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Rev.:	1.4	Author:	Zhou Weijiang
Revision History:			
1. Modify the package outline			

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Rev.:	1.3	Author:	Zhou Weijiang
Revision History:			
1. Modify the ordering information			

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Rev.:	1.2	Author:	Zhou Weijiang
Revision History:			
1. Modify "ELECTRICAL CHARACTERISTICS"			

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Rev.:	1.1	Author:	Zhou Weijiang
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3. Modify "ELECTRICAL CHARACTERISTICS(for MOSFET)", "ELECTRICAL CHARACTERISTICS" and "PACKAGE OUTLINE"			

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1. Initial release			

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